CRMJTU3400A

N-Channel 30V, 20.5mΩ Typ. Power MOSFET

Description

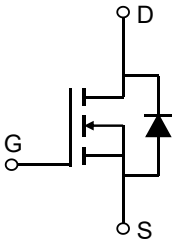
Features

- 30V, 5.8A

  $R_{DS(ON)}$ Typ = 20.5mΩ @ V_{GS} = 10V

  $R_{DS(ON)}$ Typ = 22mΩ @ V_{GS} = 4.5V

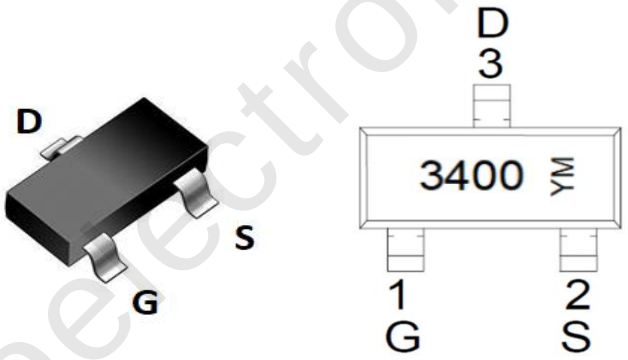
  $R_{DS(ON)}$ Typ = 26mΩ @ V_{GS} = 2.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMJTU3400A	3400	SOT-23-3L	TAPING	7"	3000	120000

Absolute Maximum Ratings (@ T_J = 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		30	V
V_{GS}	Gate-to-Source Voltage		±12	V
I_D	Continuous Drain Current	T_A = 25°C	5.8	A
		T_A = 100°C	3.48	A
I_{DM}	Pulsed Drain Current [1]		23.2	A
P_D	Power Dissipation	T_A = 25°C	1.56	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient[2]		80	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 30V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	0.5	0.9	1.5	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS} = 10V, I_D = 5.8A	-	20.5	27	mΩ
		V_{GS} = 4.5V, I_D = 5A	-	22	29	mΩ
		V_{GS} = 2.5V, I_D = 4A	-	26	35	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz	-	816	-	pF
C_{oss}	Output Capacitance		-	60	-	pF
C_{rss}	Reverse Transfer Capacitance		-	50	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 4.5V, V_{DS} = 15V, I_D = 5.8A	-	8	-	nC
Q_{gs}	Gate Source Charge		-	1.6	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	2.1	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 15V, I_D= 5.8A, R_{GEN} = 3Ω	-	5	-	ns
t_r	Turn-On Rise Time		-	7	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	40	-	ns
t_f	Turn-Off Fall Time		-	6	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	5.8	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	23.2	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = 5.8A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 3A, di/dt = 100A/us	-	8.4	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	3.3	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Test Circuit

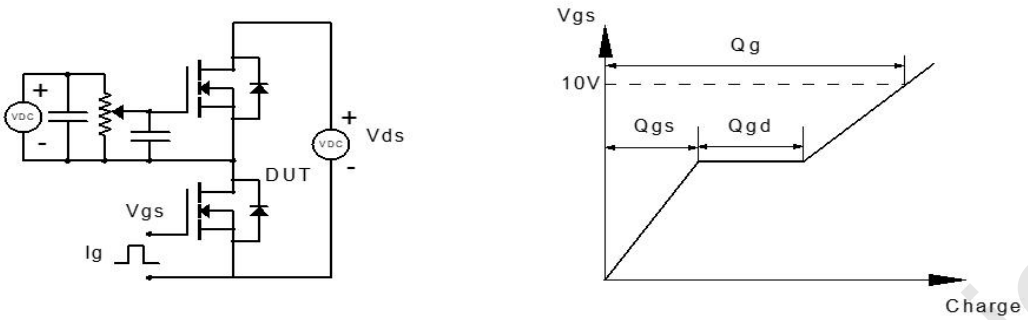


Figure 1: Gate Charge Test Circuit & Waveform

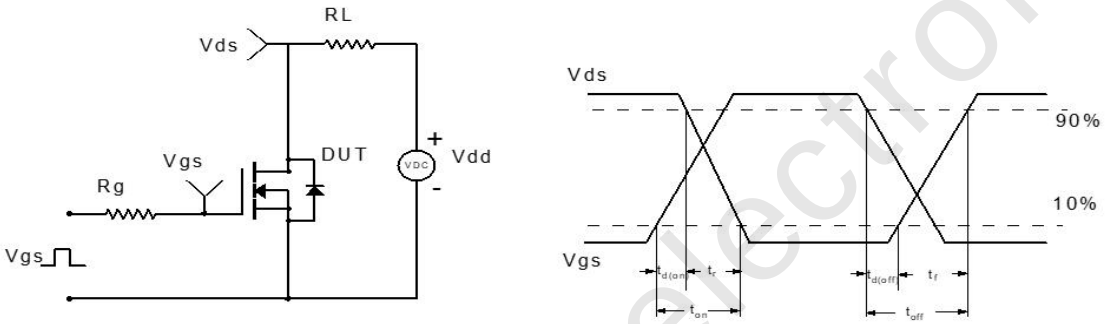


Figure 2: Resistive Switching Test Circuit & Waveform

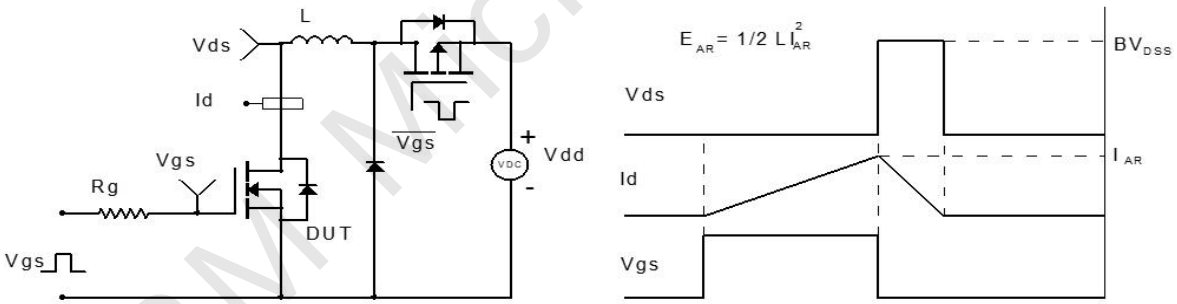


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

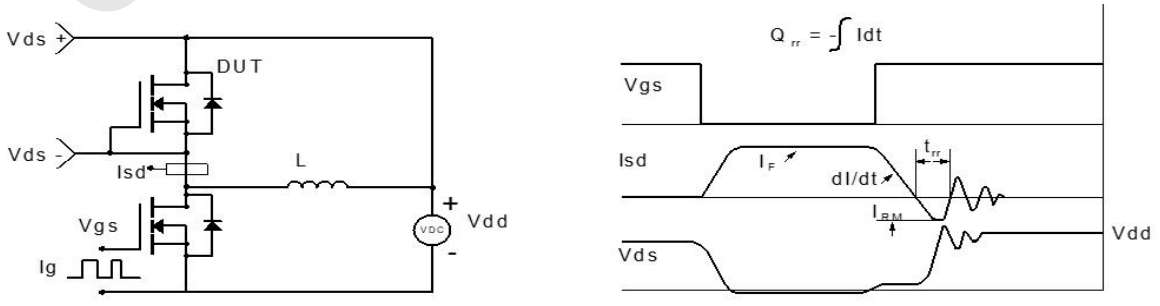
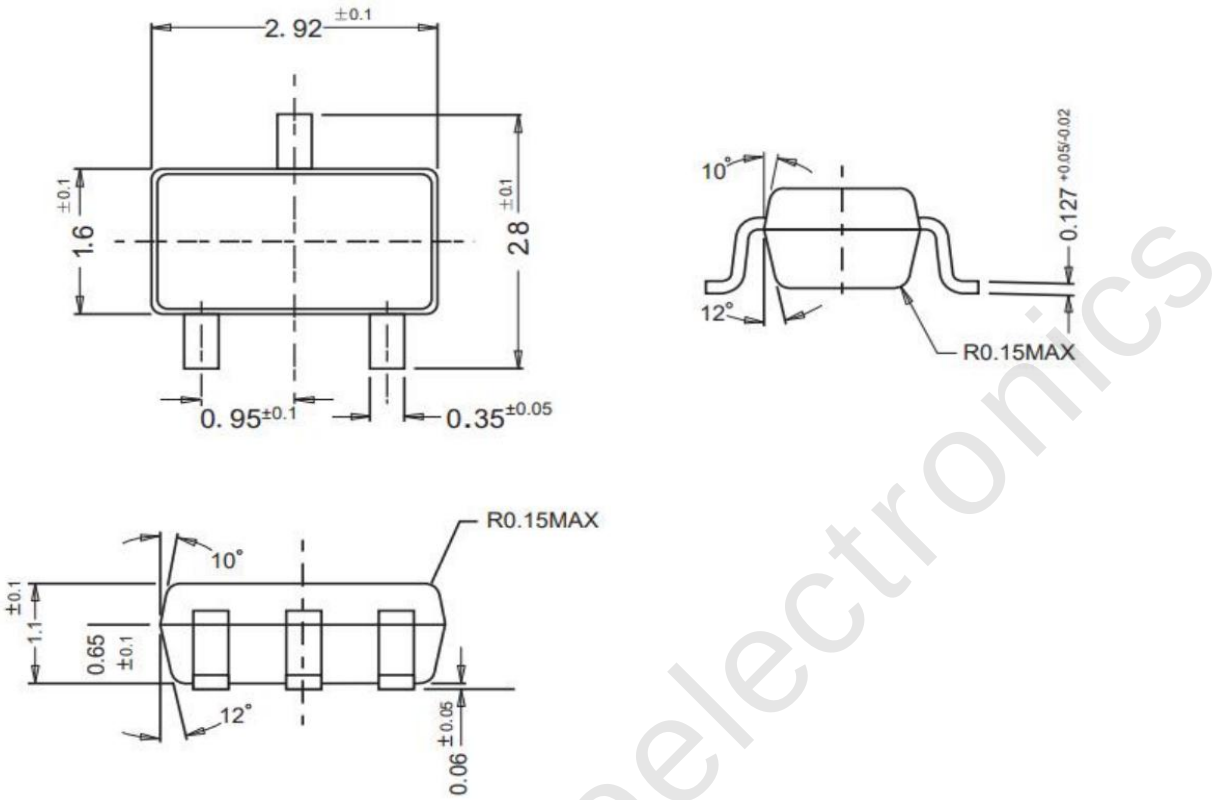


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(SOT-23-3L)



Important Notice

The information presented in datasheets is for reference only. CRM reserves the right to make changes at any time to any products or information herein, without notice.

Customers are responsible for the design and applications, including compliance with all laws, regulations and safety requirements or standards.

"Typical" parameters which provided in datasheets can vary in different applications and actual performance may vary over time. Customers are responsible for doing all necessary testing to minimize the risks associated with their applications and products.

is a registered trademark of Wuxi CRM Microelectronics Co. , Ltd.

Contact information

For more information, please visit: http://www.crm-semi.tech
For sales information, please send an email to: sales@crm-semi.com